

**isc Silicon NPN Power Transistor**

**KSD5074**

**DESCRIPTION**

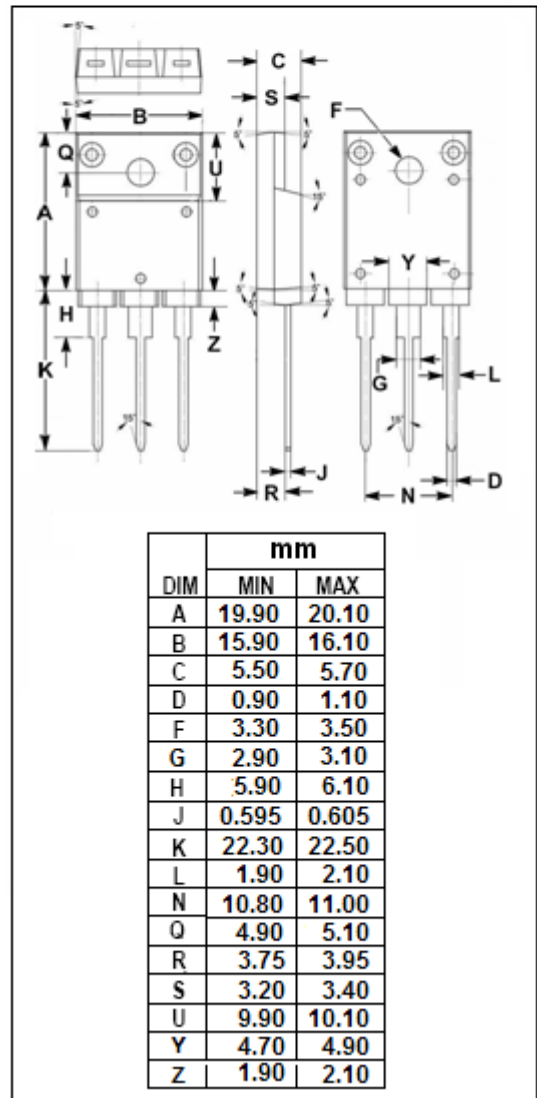
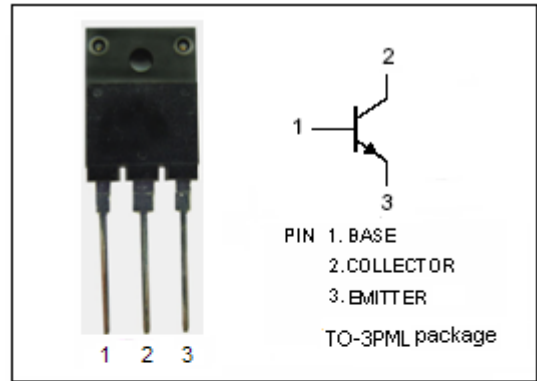
- High Breakdown Voltage-  
:  $V_{CB0} = 1500V$  (Min)
- High Switching Speed
- High Reliability

**APPLICATIONS**

- Designed for color TV horizontal output applications

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CB0}$	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current- Continuous	2.5	A
$I_{CP}$	Collector Current-Peak	10	A
$P_C$	Collector Power Dissipation @ $T_C=25^{\circ}C$	50	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-55~150	$^{\circ}C$



**isc Silicon NPN Power Transistor****KSD5074****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=2A; I_B=0.6A$			8.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=2A; I_B=0.6A$			1.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}=800V; I_E=0$			10	$\mu A$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB}=5V; I_C=0$			1	mA
$h_{FE}$	DC Current Gain	$I_C=0.5A; V_{CE}=5V$	8			
$f_T$	Current-Gain—Bandwidth Product	$I_C=0.5A; V_{CE}=10V$		3		MHz
$t_f$	Fall Time	$I_C=2A, I_{B1}=0.6A; I_{B2}=-1.2A$ $R_L=100\Omega; V_{CC}=200V$			0.4	$\mu s$